

General Description

The WSF85P06 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSF85P06 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

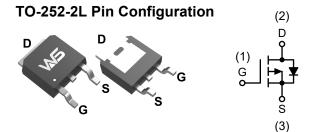
- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summery

BVDSS	RDSON	I _D
-60V	10mΩ	-85A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- CCFL Back-light Inverter



Absolute Maximum Ratings (T_{.i}= 25°C Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25℃	Continuous Drain Current, -V _{GS} @ -10V ¹	-85	Α
I _D @T _C =100°C	Continuous Drain Current, -V _{GS} @ -10V ¹	-71	А
I _{DM}	Pulsed Drain Current ²	-180	А
EAS	Single Pulse Avalanche Energy ³	450	mJ
I _{AS}	Avalanche Current	-30	Α
P _D @T _C =25°C	Total Power Dissipation ⁴	132	W
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}$
TJ	Operating Junction Temperature Range	-55 to 150	$^{\circ}$

Thermal Data

Symbol	Parameter		Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹		62.5	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		0.95	°C/W



P-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25℃ , I _D =-1mA		-0.012		V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-25A		10	12.5	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} . I _D =-250uA	-1.0	-2.0	-3.0	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	VGS-VDS , ID230UA		4.32		mV/℃
I _{DSS}	Drain-Source Leakage Current	V_{DS} =-32V , V_{GS} =0V , T_J =25 $^{\circ}$ C			1	· uA
DSS	Drain-Gource Leakage Gurrent	V_{DS} =-32V , V_{GS} =0V , T_J =55 $^{\circ}$ C			5	u.A
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-18A		12.6		S
R_g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		2.7		Ω
Qg	Total Gate Charge (-4.5V)			88		
Q_gs	Gate-Source Charge	V_{DS} =-30V , V_{GS} =-10V , I_{D} =-25A		12		nC
Q_gd	Gate-Drain Charge			21		
T _{d(on)}	Turn-On Delay Time			13		
Tr	Rise Time	V_{DD} =-30V , V_{GS} =-10V , R_{G} =6 Ω ,		15		ns
$T_{d(off)}$	Turn-Off Delay Time	I _D =-1A		60		115
T _f	Fall Time			119		
C _{iss}	Input Capacitance			4068		
C _{oss}	Output Capacitance	V _{DS} =-30V , V _{GS} =0V , f=1MHz		495		pF
C _{rss}	Reverse Transfer Capacitance			281		

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =-25V , L=0.1mH , I _{AS} =-15A	20			mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			-23	Α
I _{SM}	Pulsed Source Current ^{2,6}	VG-VD-0V , I dice current			-46	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25℃			-1	V

Note

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.
- 2.The data tested by pulsed , pulse width $\leqq 300 \text{us}$, duty cycle $\leqq 2\%$
- 3. The EAS data shows Max. rating . The test condition is V_{DD} =-25V, V_{GS} =-10V,L=1.0mH, I_{AS} =-30A
- 4.The power dissipation is limited by 150℃ junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.





P-Channel Typical Characteristics

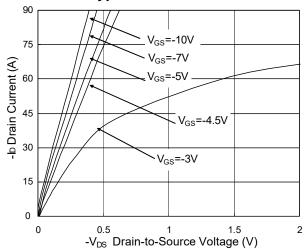


Fig.1 Typical Output Characteristics

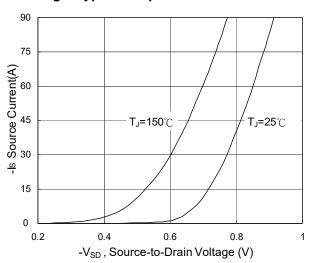


Fig.3 Forward Characteristics of Reverse

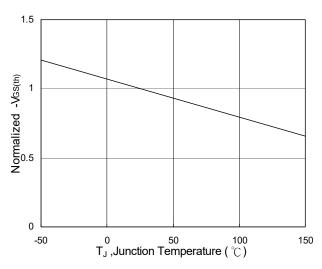


Fig.5 Normalized V_{GS(th)} v.s T_J

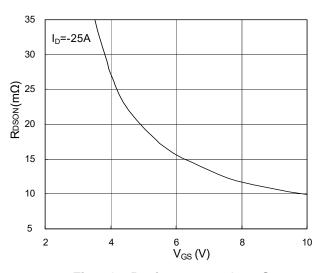


Fig.2 On-Resistance v.s Gate-Source

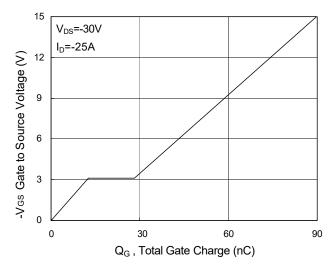


Fig.4 Gate-Charge Characteristics

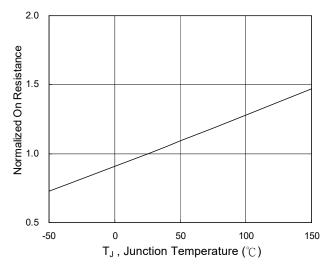
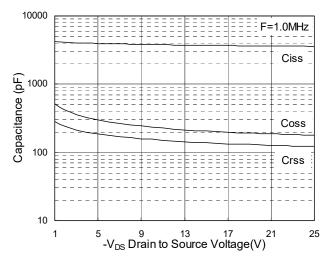


Fig.6 Normalized R_{DSON} v.s T_J





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Fig.7 Capacitance

Fig.8 Safe Operating Area

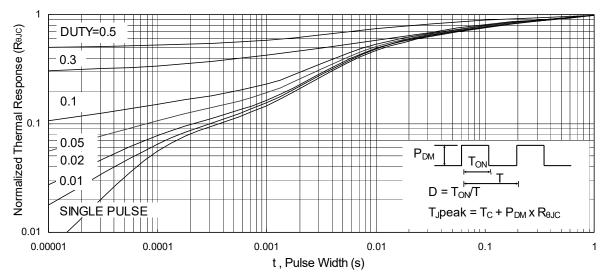
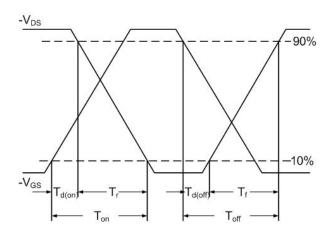


Fig.9 Normalized Maximum Transient Thermal Impedance



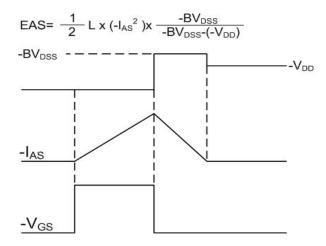
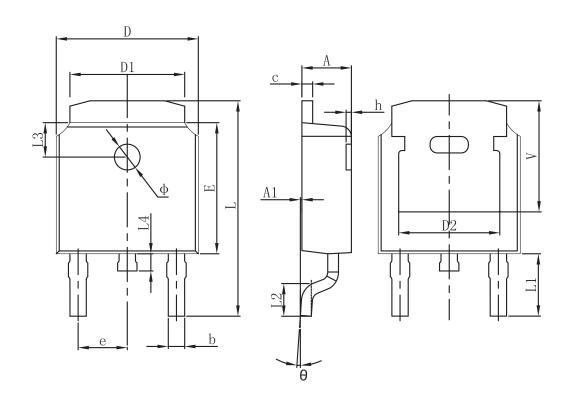


Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Waveform



Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.635	0.770	0.025	0.030	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 REF.		0.190 REF.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.712	10.312	0.382	0.406	
L1	2.900 REF.		0.114	REF.	
L2	1.400	1.700	0.055	0.067	
L3	1.600 REF.		0.063	REF.	
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.250	REF.	0.207 REF.		



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